



Substitute for form 1449A/PTO		Complete If Known	
		Application Number	10/666,034
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Filing Date	September 18, 2003
		First Named Inventor	Kocon, Christopher Boguslaw
		Art Unit	2814
		Examiner Name	Long Pham
		Attorney Docket Number	018865-009010US
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U.S. PATENT DOCUMENTS+					
Examiner Initials	Cite No. ¹	Document Number Number Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
LP	1	US-3,404,295	10-01-1968	Wamer et al.	
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	3	US-3,497,777	02-24-1970	Teszner et al.	
	4	US-3,584,356	02-16-1971	Wilson	
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	6	US-4,003,072	01-11-1977	Matsushita et al.	
	7	US-4,300,150	11-10-1981	Colak	
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	11	US-4,445,202	04-24-1984	Geotze et al.	
	12	US-4,579,621	04-01-1986	Hine	
	13	US-4,636,281	01-13-1987	Buiguez et al.	
	14	US-4,638,344	01-20-1987	Cardwell, Jr.	
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	17	US-4,716,126	12-29-1987	Cogan	
	18	US-4,746,630	05-24-1988	Hui et al.	
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	21	US-4,801,986	01-31-1989	Chang et al.	
	22	US-4,821,095	04-11-1989	Temple	
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Examiner Signature	Long Pham		Date Considered	8/81/05	

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Art Unit	2814
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Attorney Docket Number	018865-009010US

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		Number Kind Code ² (if known)			
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		Art Unit	2814
Examiner Name	Long Pham		
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U.S. PATENT DOCUMENTS+					
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	86	US-5,616,945	04-01-1997	Williams	
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	97	US-5,693,569	12-02-1997	Ueno	
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Examiner Signature	Long Pham	Date Considered	6/11/05
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First Named Inventor

Koon, Christopher Boguslaw

Art Unit

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Examiner Name

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Attorney Docket Number

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	243	US-6,608,350	08-27-2003	Kinzer et al.	
✓	244	US-6,677,641	01-13-2004	Kocon	
	245	US-2001/0023961 A1	09-27-2001	Hsieh et al.	
	246	US-2001/0028083 A1	10-11-2001	Onishi et al.	

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		Application Number	10/666,034
		Filing Date	September 18, 2003
		First Named Inventor	Kocon, Christopher Boguslaw
		Art Unit	2814
Examiner Name	Long Pham		
Sheet 7 of 12	Attorney Docket Number	018865-009010US	

U.S. PATENT DOCUMENTS+						
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code* (if known)			
LP	247	US-2001/0032998	A1	10-25-2001	Iwamoto et al.	
	248	US-2001/0041400	A1	11-15-2001	Ren et al.	
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	251	US-2002/0009832	A1	01-24-2002	Blanchard	
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	253	US-2002/0066924	A1	06-06-2002	Blanchard	
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Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ³
		Country Code ⁴	Number ⁴	Kind Code ² (if known)				
LP	259	CN	1036666A		10-25-1989			<input checked="" type="checkbox"/>
	260	DE	4300806	C1	12-23-1993	Siemens AG		<input checked="" type="checkbox"/>
	261	DE	19736981	A1	08-20-1998	Mitsubishi Denki		<input checked="" type="checkbox"/>
	262	EP	0747967	B1	02-27-2002	ST Microelectronics Inc.		<input type="checkbox"/>
	263	EP	0975024	A2	01-02-2000	Fuji Electric Co. LTD.		<input type="checkbox"/>
	264	EP	1026749	A1	08-09-2000	Mitsubishi Denki Kabushiki		<input type="checkbox"/>
	265	EP	1054451	A2	11-22-2000	Intersil Corporation		<input type="checkbox"/>
	266	EP	1205983	A1	05-15-2002	Infineon Technologies AG		<input type="checkbox"/>
	267	JP	01-192174	A	08-02-1989	Hitachi LTD.		<input checked="" type="checkbox"/>
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		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
LP	269	JP	56-058267	A	05-21-1981	Nippon Telegr & Teleph Corp.		<input checked="" type="checkbox"/>
	270	JP	62-069562		03-30-1987	Mitsubishi Electric Corp		<input checked="" type="checkbox"/>
	271	JP	63-186475		08-02-1988	Nissan Motor Co. LTD.		<input checked="" type="checkbox"/>
	272	JP	63-288047		11-25-1988	Toshiba Corp.		<input checked="" type="checkbox"/>
	273	JP	64-022051		01-25-1989	Matsushita Electric Ind		<input checked="" type="checkbox"/>
	274	JP	2000-040822		02-08-2000	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	275	JP	2000-040872		02-08-2000	Sanju Metal IND CO LTD.		<input checked="" type="checkbox"/>
	276	JP	2000-156978	A	06-06-2000	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	277	JP	2000-277726	A	10-06-2000	Toshiba Corp.		<input checked="" type="checkbox"/>
	278	JP	2000-277728	A	10-06-2000	NEC Kansai LTD.		<input checked="" type="checkbox"/>
	279	JP	2001-015448		01-19-2001	Toshiba Corp.		<input checked="" type="checkbox"/>
	280	JP	2001-015752		01-19-2001	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	281	JP	2001-102577	A	04-13-2001	Toshiba Corp.		<input checked="" type="checkbox"/>
	282	JP	2001-111041	A	04-20-2001	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	283	JP	2001-135819	A	05-18-2001	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	284	JP	2001-144292	A	05-25-2001	Denso Corp.		<input checked="" type="checkbox"/>
	285	JP	2001-244461	A	09-07-2001	Toyota Central Res & Dev Lab INC.		<input checked="" type="checkbox"/>
	286	JP	2001-313391	A	12-20-2001	S. Takahiro et al.		<input checked="" type="checkbox"/>
	287	JP	2002-083976	A	03-22-2002	Naito et al.		<input checked="" type="checkbox"/>
	288	PCT	WO 00/33386	A2	08-08-2000	Koninklijke Philips Electronics		<input type="checkbox"/>
	289	PCT	WO 00/68997	A1	11-16-2000	C.P. Clare Corporation		<input type="checkbox"/>
	290	PCT	WO 00/68998	A1	11-16-2000	C.P. Clare Corporation		<input type="checkbox"/>
	291	PCT	WO 00/75965	A2	12-14-2000	General Semiconductor, Inc.		<input type="checkbox"/>
	292	PCT	WO 01/06550	A1	01-23-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	293	PCT	WO 01/06557	A1	01-25-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	294	PCT	WO 01/45155	A1	06-21-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	295	PCT	WO 01/59847	A2	08-16-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	296	PCT	WO 01/71815		09-27-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	297	PCT	WO 01/95385	A1	12-13-2001	General Semiconductor, Inc.		<input type="checkbox"/>

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			Application Number	10/666,034	
			Filing Date	September 18, 2003	
			First Named Inventor	Kocon, Christopher Boguslaw	
			Art Unit	2814	
Examiner Name	Long Pham				
Sheet	9	of	12	Attorney Docket Number	018865-009010US

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		Country Code ²	Number ⁴	Kind Code ⁵ (if known)				
LP	298	PCT	WO 01/95398	A1	12-13-2001	General Semiconductor, Inc.		<input type="checkbox"/>
	299	PCT	WO 02/01644	A2	01-03-2002	Silicon Wireless Corporation		<input type="checkbox"/>
↓	300	PCT	WO 02/047171	A1	06-13-2002	International Rectifier Corporation		<input type="checkbox"/>
								<input type="checkbox"/>
								<input type="checkbox"/>
								<input type="checkbox"/>
								<input type="checkbox"/>
								<input type="checkbox"/>

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		Examiner Name	Long Pham		
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	310	"CoolMOS™ the second generation," <i>Infineon Technologies product information</i> , (2000), 2 pages total.	
	311	CURTIS, et al. "APCVD TEOS: 03 Advanced Trench Isolation Applications," <i>Semiconductor Fabtech 9th Edition (1999)</i> 8 pages total.	
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✓	316	GLENN et al. "A Novel Vertical Deep Trench RESURF DMOS (VTR-DMOS)" <i>IEEE ISPD 2000, May 22-25, Toulouse France</i> , pp. 197-200.	

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LP	317	"IR develops CoolMOS™ -equivalent technology, positions it at the top of a 3-tiered line of new products for SMPS," International Rectifiers company information available at http://www.irf.com (1999) 3 pages total.	
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	326	PARK et al., "Lateral Trench Gate Super-Junction SOI-LDMOSFETs with Low On-Resistance," <u>Institute for Microelectronics, University of Technology Vienna, Austria</u> (2002), pp. 283-285.	
	327	SAKAI et al., "Experimental investigation of dependence of electrical characteristics of device parameters in trench MOS barrier, schottky diodes," (1998) <u>International Symposium on Power Semiconductors and ICs, Technical Digest</u> , pp. 293-296.	
	328	SHENAI et al., "Current transport mechanisms in atomically abrupt metal-semiconductor interfaces," (April 1988) <u>IEEE Transactions on Electron Devices</u> , Vol. 35, No. 4, pp. 468-482.	
	329	SHENAI et al., "Monolithically integrated power MOSFET and schottky diode with improved reverse recovery characteristics," (April 1990) <u>IEEE Transactions on Electron Devices</u> , Vol. 37, No. 4, pp. 1167-1169.	
	330	SHENOY et al. "Analysis of the Effect of Charge Imbalance on the Static and Dynamic Characteristic of the Super Junction MOSFET," <u>IEEE International Symposium on Power Semiconductor Devices 1999</u> , pp. 99-102 (1999).	
	331	SINGER "Empty Spaces in Silicon (ESS): An Alternative to SOI," <u>Semiconductor International</u> page 42, December 1999.	
V	332	TABISZ et al., "A MOSFET resonant synchronous rectifier for high-frequency dc/dc converters," (1990) <u>Proc. IEEE Power Electronics Specialist Conf. (PESC)</u> , pp. 769-779.	

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L P	333	Technical Literature from Quester Technology, Model APT-4300 300mm Atmospheric TEOS/Ozone CVD System, (unknown date), 3 pages total.	
	334	Technical Literature from Quester Technology, Model APT-6000 Atmospheric TEOS-Ozone CVD System, (unknown date), 2 pages total.	
	335	Technical Literature from Silicon Valley Group Thermal Systems, APNext, High Throughput APCVD Cluster Tool for 200 mm/300 mm Wafer Processing, (unknown date), 2 pages total.	
	336	TU et al. "On the reverse blocking characteristics of schottky power diodes," (December 1992) <i>IEEE Transactions on Electron Devices</i> . Vol. 39, No. 12, pp. 2813-2814 2 pages total.	
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	340	YAMASHITA et al., "Conduction Power loss in MOSFET synchronous rectifier with parallel-connected schottky barrier diode, (July 1998) <i>IEEE Transactions on Power electronics</i> , Vol. 13, No. 4, pp. 667-673.	

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